

客户名稱 CUSTOMER	:	
客户料號 CUSTOMER'S P/N	:	
料號 PART NUMBER	:	WAN3216F245C04
規格 DESCRIPTION	:	Chip Antenna 3216 L Ant 2.45G Type 04
版本 VERSION	:	V1.2
日期 ISSUE DATE	:	2020/02/27



	工 程 部 R&D CENTER	
承 認 APPROVAL	確認 CHECKED	製 作 DRAWN
Ray	Tennyson	Snow



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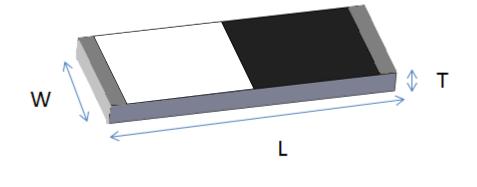
OneWave Electronic Co., Ltd.

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3216 Chip antenna

For Bluetooth / WLAN Applications



P/N: WAN3216F245C04

	Dimension (mm)				
L	3.23 ± 0.20				
W	1.66 ± 0.20				
Т	0.45 ± 0.20				

Part Number Information

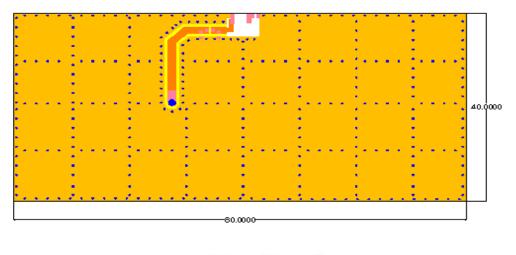
WA	<u>AN</u>	<u>3216</u>	<u>F</u>	<u>245</u>	<u>C</u>	<u>04</u>
A	•	В	С	D	Ε	F
Α	l	Product Se	ries		Antenna	
B	Dimension L x W			3.2 x 1.6mm (±0.2mm)		
С	Material			Hig	h K mate	erial
D	Working Frequency			2.	4 ~ 2.5G	Hz
Ε	Feeding mode			PIFA &	Single F	eeding
F	Antenna type			•	Туре = 04	1

1. Electrical Specification

Specification						
Part Number	WAN3216F245C04					
Central Frequency	2450	MHz				
Bandwidth	120 (Min.)	MHz				
Return Loss	-6.5 (Max)	dB				
Peak Gain	1.75	dBi				
Impedance	50	Ohm				
Operating Temperature	-40~+110	°C				
Maximum Power	4	W				
Resistance to Soldering Heats	10 (@ 260°C)	sec.				
Polarization	Linear					
Azimuth Beamwidth	Omni-directional					
Termination	Ni / Au (Leadless)					

Remark : Bandwidth & Peak Gain was measured under evaluation board of next page

2. Recommended PCB Pattern Evaluation Board Dimension



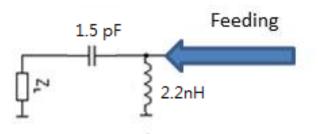


2nd Evaluation Board Dimension

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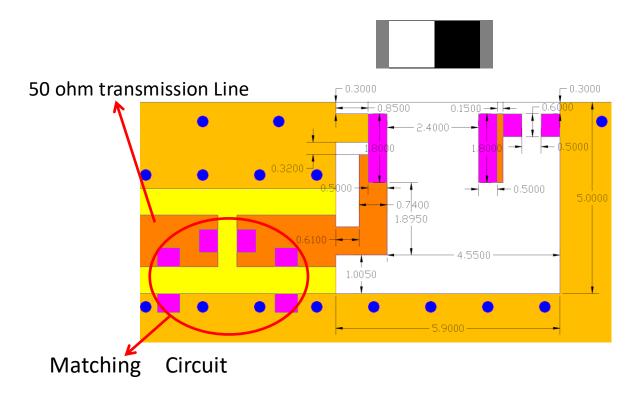
Suggested Matching Circuit

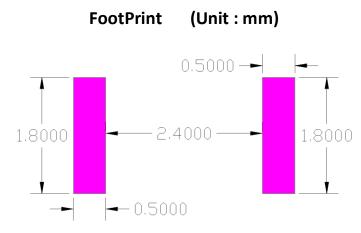
<u>重要資訊:</u> 匹配元件建議使用精準度高的電感±0.1~0.3nH、電容±0.1pF



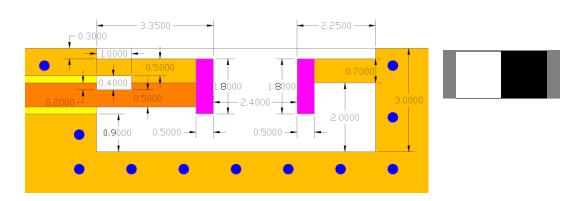


Layout Dimensions in Clearance area(Size=5.9*5.0mm)

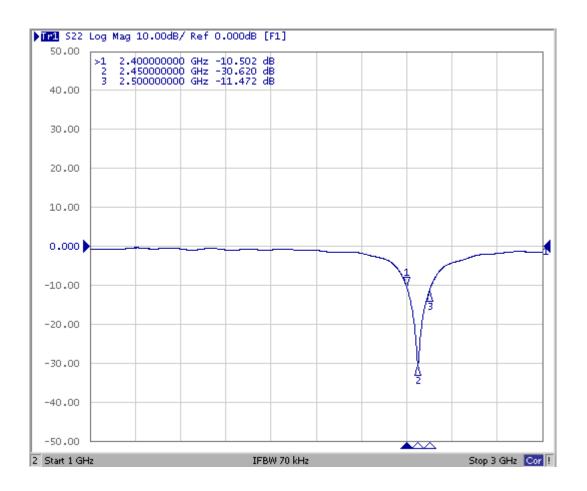




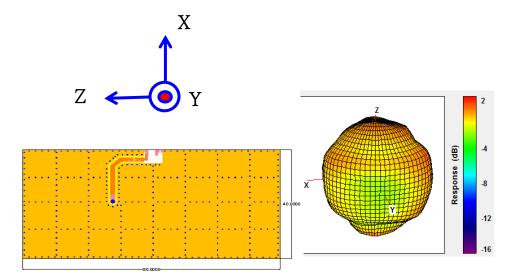
• 2nd Layout Dimensions in Clearance area(Size=8.0*3.0mm)



3. Measurement Results Return Loss

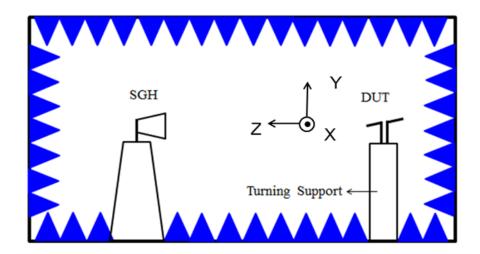


Radiation Pattern



	Efficiency	Peak Gain	Directivity
2400MHz	82.36%	1.69 dBi	2.53 dBi
2450MHz	85.65%	1.75 dBi	2.42 dBi
2500MHz	83.88%	1.71 dBi	2.47 dBi

Chamber Coordinate System





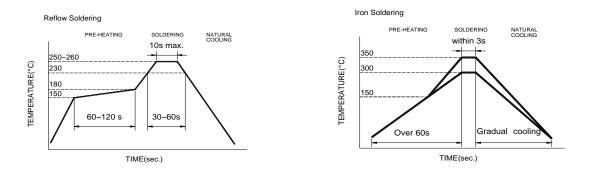
4.Reliability and Test Condictions

BA	-			TEST CONDITION		
ITEM Soldorability		REMENTS	worago	TEST CONDITION		
Solderability	 Wetting shall exceed 90% coverage No visible mechanical damage 			Pre-heating temperature:150°C/60sec.		
	2.110 1010	ie meenamear aamag	J C	Solder temperature:230 \pm 5 $^{\circ}$ C		
		TEMP (℃)		Duration:4±1sec.		
				Solder:Sn-Ag3.0-Cu0.5		
		230°C	4±1 sec.	Flux for lead free: rosin		
			/			
		150℃				
		6	Sosec			
Solder heat		le mechanical damag		Pre-heating temperature:150°C/60sec.		
Resistance	2. Central	Freq. change :within	± 6%	Solder temperature:260 \pm 5 $^{\circ}$ C		
	-	TEMP (°C)		Duration:10±0.5sec.		
			10105	Solder:Sn-Ag3.0-Cu0.5		
		260°C	10±0.5 sec.	Flux for lead free: rosin		
		150°C	$ \rightarrow $			
			0sec			
		/ 0	USEC \			
Component Adhesion	1. No visib	le mechanical damag	ge	The device should be reflow		
Adnesion (Push test)				soldered(230 \pm 5 $^{\circ}$ C for 10sec.) to a tinned		
				copper substrate A dynometer force		
				gauge should be applied the side of the		
				component. The device must with-ST-F 0.5 Kg without failure of the termination		
				attached to component.		
Component	1. No visib	le mechanical damag	je	Insert 10cm wire into the remaining open		
Adhesion				eye bend ,the ends of even wire lengths		
(Pull test)				upward and wind together.		
(i un test)				Terminal shall not be remarkably		
				damaged.		
Thermal shock	1 Novi	isible mechanic	al damaga	+110°C=>30±3min		
				-40°C=>30±3min		
	Z. Cent	ral Freq. change	e :witnin ±6%	Test cycle:10 cycles		
	Phase	Temperature(°C)	Time(min)	The chip shall be stabilized at normal		
	1	+110±5 ℃	30±3	condition for 2~3 hours before		
	2	Room	Within	measuring.		
	2	Temperature	3sec	medsunng.		
	3	-40±2℃	30±3			
	3	40 <u>12</u> ()	30±3			
		Doom	\//ithin			
	4	Room	Within			
	4	Room Temperature	Within 3sec			
Resistance to		Temperature	3sec	Temperature: +110±5°C		
	1. No vis	Temperature sible mechanical	3sec damage	Temperature: +110±5°C Duration: 1000±12hrs		
High	1. No vis 2. Centra	Temperature sible mechanical al Freq. change :	3sec damage within ±6%	Duration: 1000±12hrs		
High	1. No vis 2. Centra	Temperature sible mechanical	3sec damage within ±6%	Duration: 1000±12hrs The chip shall be stabilized at normal		
High	1. No vis 2. Centra	Temperature sible mechanical al Freq. change :	3sec damage within ±6%	Duration: 1000±12hrs The chip shall be stabilized at normal condition for 2~3 hours before		
High Temperature	1. No vis 2. Centra 3. No dis	Temperature sible mechanical al Freq. change : sconnection or sh	3sec damage within ±6% nort circuit.	Duration: 1000±12hrs The chip shall be stabilized at normal condition for 2~3 hours before measuring.		
High Temperature Resistance to	1. No vis 2. Centra 3. No dis 1. No vis	Temperature sible mechanical al Freq. change : sconnection or sh sible mechanical	3sec damage within ±6% nort circuit. damage	Duration: 1000±12hrs The chip shall be stabilized at normal condition for 2~3 hours before measuring. Temperature:-40±5°C		
High Temperature Resistance to Low	1. No vis 2. Centra 3. No dis 1. No vis 2. Centra	Temperature sible mechanical al Freq. change : sconnection or sh sible mechanical al Freq. change :	3sec damage within ±6% nort circuit. damage within ±6%	Duration: 1000±12hrs The chip shall be stabilized at normal condition for 2~3 hours before measuring. Temperature:-40±5°C Duration: 1000±12hrs		
High Temperature Resistance to Low	1. No vis 2. Centra 3. No dis 1. No vis 2. Centra	Temperature sible mechanical al Freq. change : sconnection or sh sible mechanical	3sec damage within ±6% nort circuit. damage within ±6%	Duration: 1000±12hrs The chip shall be stabilized at normal condition for 2~3 hours before measuring. Temperature:-40±5°C Duration: 1000±12hrs The chip shall be stabilized at normal		
High Temperature Resistance to Low	1. No vis 2. Centra 3. No dis 1. No vis 2. Centra	Temperature sible mechanical al Freq. change : sconnection or sh sible mechanical al Freq. change :	3sec damage within ±6% nort circuit. damage within ±6%	 Duration: 1000±12hrs The chip shall be stabilized at normal condition for 2~3 hours before measuring. Temperature:-40±5°C Duration: 1000±12hrs The chip shall be stabilized at normal condition for 2~3 hours before 		
High Temperature Resistance to Low Temperature	1. No vis 2. Centra 3. No dis 1. No vis 2. Centra 3. No dis	Temperature sible mechanical al Freq. change : sconnection or sh sible mechanical al Freq. change : sconnection or sh	3sec damage within ±6% nort circuit. damage within ±6% nort circuit.	 Duration: 1000±12hrs The chip shall be stabilized at normal condition for 2~3 hours before measuring. Temperature:-40±5°C Duration: 1000±12hrs The chip shall be stabilized at normal condition for 2~3 hours before measuring. 		
High Temperature Resistance to Low Temperature	1. No vis 2. Centra 3. No dis 1. No vis 2. Centra 3. No dis	Temperature sible mechanical al Freq. change : sconnection or sh sible mechanical al Freq. change :	3sec damage within ±6% nort circuit. damage within ±6% nort circuit.	 Duration: 1000±12hrs The chip shall be stabilized at normal condition for 2~3 hours before measuring. Temperature:-40±5°C Duration: 1000±12hrs The chip shall be stabilized at normal condition for 2~3 hours before measuring. Temperature: 40±2°C 		
High Temperature Resistance to Low Temperature	1. No vis 2. Centra 3. No dis 1. No vis 2. Centra 3. No dis 1. No vis	Temperature sible mechanical al Freq. change : sconnection or sh sible mechanical al Freq. change : sconnection or sh	3sec damage within ±6% nort circuit. damage within ±6% nort circuit. damage	 Duration: 1000±12hrs The chip shall be stabilized at normal condition for 2~3 hours before measuring. Temperature:-40±5°C Duration: 1000±12hrs The chip shall be stabilized at normal condition for 2~3 hours before measuring. Temperature: 40±2°C Humidity: 90% to 95% RH 		
High Temperature Resistance to Low Temperature	1. No vis 2. Centra 3. No dis 1. No vis 2. Centra 3. No dis 1. No vis 2. Centra	Temperature sible mechanical al Freq. change : sconnection or sh sible mechanical al Freq. change : sconnection or sh sible mechanical al Freq. change :	3sec damage within ±6% nort circuit. damage within ±6% nort circuit. damage within ±6%	 Duration: 1000±12hrs The chip shall be stabilized at normal condition for 2~3 hours before measuring. Temperature:-40±5°C Duration: 1000±12hrs The chip shall be stabilized at normal condition for 2~3 hours before measuring. Temperature: 40±2°C Humidity: 90% to 95% RH Duration: 1000±12hrs 		
High Temperature Resistance to	1. No vis 2. Centra 3. No dis 1. No vis 2. Centra 3. No dis 1. No vis 2. Centra	Temperature sible mechanical al Freq. change : sconnection or sh sible mechanical al Freq. change : sconnection or sh sible mechanical	3sec damage within ±6% nort circuit. damage within ±6% nort circuit. damage within ±6%	 Duration: 1000±12hrs The chip shall be stabilized at normal condition for 2~3 hours before measuring. Temperature:-40±5°C Duration: 1000±12hrs The chip shall be stabilized at normal condition for 2~3 hours before measuring. Temperature: 40±2°C Humidity: 90% to 95% RH 		
High Temperature Resistance to Low Temperature	1. No vis 2. Centra 3. No dis 1. No vis 2. Centra 3. No dis 1. No vis 2. Centra	Temperature sible mechanical al Freq. change : sconnection or sh sible mechanical al Freq. change : sconnection or sh sible mechanical al Freq. change :	3sec damage within ±6% nort circuit. damage within ±6% nort circuit. damage within ±6%	 Duration: 1000±12hrs The chip shall be stabilized at normal condition for 2~3 hours before measuring. Temperature:-40±5°C Duration: 1000±12hrs The chip shall be stabilized at normal condition for 2~3 hours before measuring. Temperature: 40±2°C Humidity: 90% to 95% RH Duration: 1000±12hrs 		

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5.Soldering and Mounting

Mildly activated rosin fluxes are preferred. The minimum amount of solder can lead to damage from the stresses caused by the difference in coefficients of expansion between solder, chip and substrate. The terminations are suitable for all wave and re-flow soldering systems. If hand soldering cannot be avoided, the preferred technique is the utilization of hot air soldering tools.



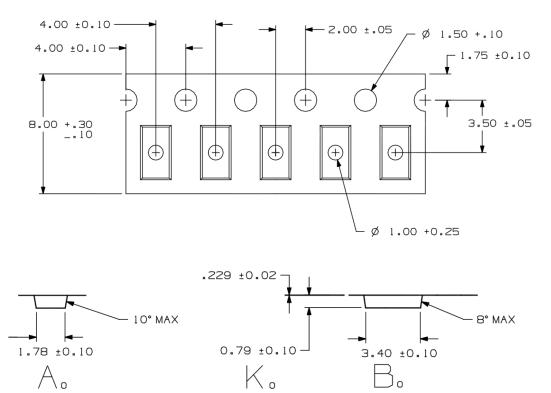
Recommended temperature profiles for re-flow soldering in Figure 1.

Products attachment with a soldering iron is discouraged due to the inherent process control limitations. In the event that a soldering iron must be employed the following precautions are recommended.

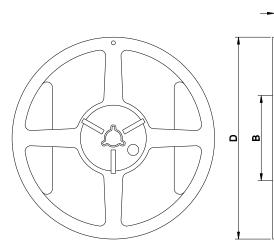
- Preheat circuit and products to 150° C
- · Never contact the ceramic with the iron tip
- · Use a 20 watt soldering iron with tip diameter of 1.0mm
- 280°C tip temperature (max)
- 1.0mm tip diameter (max)
- Limit soldering time to 3 sec.

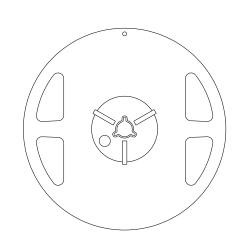
6.Packaging Information

Tape Specification:









7" x 8 mm

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Tape Width(mm)	A(mm)	B(mm)	C(mm)	D(mm)	Chip/Reel(pcs)
8	9.0±0.5	60±2	13.5±0.5	178±2	3000

7. Storage and Transportation Information

Storage Conditions

To maintain the solderability of terminal electrodes:

- 1. Temperature and humidity conditions: -10~ 40° C and 30~70% RH.
- 2. Recommended products should be used within 6 months from the time of delivery.
- 3. The packaging material should be kept where no chlorine or sulfur exists in the air.

Transportation Conditions

- 1. Products should be handled with care to avoid damage or contamination from perspiration and skin oils.
- 2. The use of tweezers or vacuum pick up is strongly recommended for individual components.
- 3. Bulk handling should ensure that abrasion and mechanical shock are minimized.